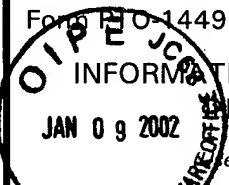


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	Applicant Protigal et al.	
	Filing Date February 2, 2001	Group Art Unit 2826

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
AS	3,699,722	10/1 972	Davidson et al.			
	4,061,999	12/1977	Proebsting et al.			
	4,271,461	06/1981	Hoffmann et al.			
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	4,566,081	01/1986	Ochii			
	4,587,639	05/1986	Aoyama et al.			
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	4,658,379	04/1987	Fujishima et al.			

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	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO
AS	56-148859	11/1981	Japan			X	
	56-153778	11/1981	Japan			X	
	57-001902	01/1982	Japan			X	
	01-268032	10/1989	Japan			X (only)	

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AS	McKenny, Verron D., "Good bits swapped for bad in 64-kilobit E-PROM," pps. 115-120 plus Cover and Table of Contents, <u>Electronics</u> , March 13, 1990.
AS	Natori et al., "FAM: 16.5: A 34ns 256K DRAM," pps. 232-233 plus Cover and Table of Contents, <u>IEEE International Solid-State Circuits Conference</u> , February 25, 1983.
	<u>Research Disclosure</u> , (3 pages), June 1985.

EXAMINER AS	DATE CONSIDERED 11-29-02
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Docket Number (Optional)
2898.2US (88-070.7)Application Number
09/776,387Applicant **Protigal et al.**Filing Date **February 2, 2001**Group Art Unit **2826**

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EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
A.S.	4,716,549	12/1987	Nakano et al.			
	4,730,276	03/1988	Waller			
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	4,780,851	10/1988	Kurakami			
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	4,829,480	05/1989	Seo			
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	4,943,960	07/1990	Komatsu et al.			
	4,987,325	01/1991	Seo			
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	5,038,325	08/1991	Douglas et al.			
	5,042,011	08/1991	Casper et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
						YES	NO

OTHER DOCUMENTS

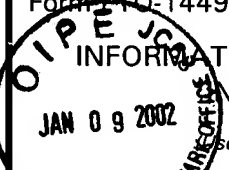
(Including Author, Title, Date, Pertinent Pages, Etc.)

A.S.		"Decoupling Capacitor Structure to Reduce FET Output Driver Switching Noise," pps. 167-168, <u>IBM Technical Disclosure Bulletin</u> , Vol 30., No. 7, December 1987.
A.S.		"MOS Memory," (4 pages), <u>Toshiba Mos Memory Products Data Book</u> , April 1987.
A.S.		"Double-Traversing Pseudo-Folded-Bitline Design for Cross-Point Memory Cells," pps. 246-248, <u>IBM Technical Disclosure Bulletin</u> , Vol. 30, No. 11, April 1988.

EXAMINER

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	Applicant Protigal et al.	
	Filing Date February 2, 2001	Group Art Unit 2826

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A.S.	5,177,908	01/1993	Tuttle			
	RE 34,425	11/1993	Schultz			
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	RE 35,825	06/1998	Zager			

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						YES	NO

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A.S.	"New Memory Products 1987/1988," (4 pages), <u>NEC Electronics Inc. Supplement to 1986 Memory Products Data Book</u> , December 1987.
A.S.	Gillingham et al., "High-Speed, High-Reliability Circuit Design for Megabit DRAM," pps. 1171-1175 plus Table of Contents, <u>IEEE Journal of Solid-State Circuits</u> , Vol 26, No. 8, August 1991.
A.S.	"IBM's Response to Micron," (22 pages), December 8, 1995.

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